

Arash Salemi

List of Publications by Year in descending order

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222
citing authors

#	ARTICLE	IF	CITATIONS
1	15 kV-Class Implantation-Free 4H-SiC BJTs With Record High Current Gain. IEEE Electron Device Letters, 2018, 39, 63-66.	3.9	37
2	Time-Dependent Dielectric Breakdown of Commercial 1.2 kV 4H-SiC Power MOSFETs. IEEE Journal of the Electron Devices Society, 2021, 9, 633-639.	2.1	30
3	5.8-kV Implantation-Free 4H-SiC BJT With Multiple-Shallow-Trench Junction Termination Extension. IEEE Electron Device Letters, 2015, 36, 168-170.	3.9	25
4	500 Å°C High Current 4H-SiC Lateral BJTs for High-Temperature Integrated Circuits. IEEE Electron Device Letters, 2017, 38, 1429-1432.	3.9	22
5	Conductivity modulated on-axis 4H-SiC 10+kV PiN diodes. , 2015, , .		18
6	Gate Leakage Current and Time-Dependent Dielectric Breakdown Measurements of Commercial 1.2 kV 4H-SiC Power MOSFETs. , 2019, , .		14
7	Area- and efficiency-optimized junction termination for a 5.6 kV SiC BJT process with low ON-resistance. , 2015, , .		13
8	A Wafer-Scale Ni-Salicide Contact Technology on n-Type 4H-SiC. ECS Journal of Solid State Science and Technology, 2017, 6, P197-P200.	1.8	13
9	Gate Oxide Reliability Studies of Commercial 1.2 kV 4H-SiC Power MOSFETs. , 2020, , .		12
10	Optimal Emitter Cell Geometry in High Power 4H-SiC BJTs. IEEE Electron Device Letters, 2015, 36, 1069-1072.	3.9	9
11	Low Temperature Ni-Al Ohmic Contacts to p-Type 4H-SiC Using Semi-Salicide Processing. Materials Science Forum, 0, 924, 389-392.	0.3	9
12	Area-Optimized JTE for 4.5 kV Non Ion-Implanted 4H-SiC BJT. Materials Science Forum, 0, 740-742, 974-977.	0.3	8
13	Threshold Voltage Instability of Commercial 1.2 kV SiC Power MOSFETs. , 2020, , .		8
14	Investigation of the Breakdown Voltage in High Voltage 4H-SiC BJT with Respect to Oxide and Interface Charges. Materials Science Forum, 0, 821-823, 834-837.	0.3	7
15	Modification of Etched Junction Termination Extension for the High Voltage 4H-SiC Power Devices. Materials Science Forum, 2016, 858, 978-981.	0.3	7
16	Conductivity Modulated and Implantation-Free 4H-SiC Ultra-High-Voltage PiN Diodes. Materials Science Forum, 0, 924, 568-572.	0.3	7
17	Fabrication and Design of 10 kV PiN Diodes Using On-Axis 4H-SiC. Materials Science Forum, 0, 778-780, 836-840.	0.3	6
18	Intertwined Design: A Novel Lithographic Method to Realize Area Efficient High-Voltage SiC BJTs and Darlington Transistors. IEEE Transactions on Electron Devices, 2016, 63, 4366-4372.	3.0	6

#	ARTICLE	IF	CITATIONS
19	Design Strategies for Rugged SiC Power Devices. , 2019, , .		6
20	The IMOSFET: A Deeply-Scaled Fully-Self-Aligned Trench MOSFET. Materials Science Forum, 0, 1004, 751-757.	0.3	5
21	High Temperature Bipolar Master-Slave Comparator and Frequency Divider in 4H-SiC Technology. Materials Science Forum, 0, 897, 681-684.	0.3	4
22	A Comprehensive Study on the Geometrical Effects in High-Power 4H-SiC BJTs. IEEE Transactions on Electron Devices, 2017, 64, 882-887.	3.0	4
23	JFET Region Design Trade-Offs of 650 V 4H-SiC Planar Power MOSFETs. Solid State Electronics Letters, 2021, 3, 53-58.	1.0	4
24	Geometrical Effect Dependency on the On-State Characteristics in 5.6 kV 4H-SiC BJTs. Materials Science Forum, 0, 858, 958-961.	0.3	3
25	4.5-kV 20-m ² Implantation-Free 4H-SiC BJT with Trench Structures on the Junction Termination Extension. Materials Science Forum, 0, 821-823, 838-841.	0.3	2
26	Process Variation Tolerant 4H-SiC Power Devices Utilizing Trench Structures. Materials Science Forum, 2013, 740-742, 809-812.	0.3	1
27	10+ kV Implantation-Free 4H-SiC PIN Diodes. Materials Science Forum, 2017, 897, 423-426.	0.3	1